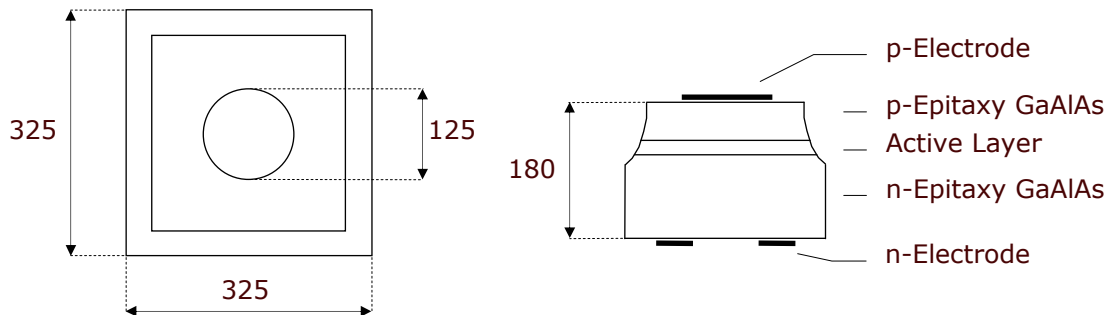


RED

Item No.: 115261 L

1. This specification applies to GaAlAs / GaAlAs LED Chips (substrate removed)
2. Structure
 - 2.1 Mesa structure
 - 2.2 Electrodes

p-side (anode)	Au alloy
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



Wire-bond contacts can also be square

4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	V_F	$I_F = 20 \text{ mA}$		1,85	2,20	V
Reverse current	I_R	$V_R = 5 \text{ V}$			10	μA
Luminous intensity	I_V	$I_F = 10 \text{ mA}$	8,0	11,0		mcd
Luminous intensity	I_V	$I_F = 20 \text{ mA}$	16,0	22,0		mcd
Output power	Φ_e	$I_F = 20 \text{ mA}$	1,3	1,6		mW
Peak wavelength	λ_p	$I_F = 20 \text{ mA}$		670		nm

power measurement at OSA on gold plate

5. Packing

Dice on adhesive film with 1) wire-bond side on top
2) back contact on top

6. Labeling

Type	Lot No.	I_V typ min max	Quantity